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## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Complete if Known					
Application Number	10/762,181				
Filing Date	January 21, 2004				
First Named Inventor	Mohklesi				
Art Unit	2827				
Examiner Name	Huan Hoang				
Attorney Docket Number	SAND-01021US0				

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Examiner Initials*	Cite No.	Document Number  Number-Kind Code <sup>2 (f boom)</sup>	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Wh Relevant Passages or Relev Figures Appear	
W		US- 5,043,940	8/27/1991	Harari		
F		<sup>US-</sup> 5,095,344	3/10/1992	Harari		
		US- 5,172,338	12/15/1992	Mehrotra et al.		
		US- 5,343,063	8/30/1994	Yuan et al.		
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WY		<sup>US-</sup> 6,151,248	11/21/2000	Harari et al.		

		FORE	IGN PATENT DOCU	MENTS		
	Cite No.	Foreign Patent Document	Publication Date	Name of Patentee or Applicant of Cited Document	Peges, Columns, Lines, Where Relevant Passages	
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Substitute for form 1449/PTO	Application Number	10/762,181	_		
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INFORMATION DISCLOSURE	First Named Inventor	Mohklesi	_		
STATEMENT BY APPLICANT	Art Unit	2827	_		
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			U. S. PATEN	T DOCUMENTS		
Examiner Initiats*	Cite No.1	Document Number  Number-Kind Code <sup>3 (* known)</sup>	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
W		US- 6222762	4/24/2001	Guterman et al.		
6 4		US- 6246607	6/12/2001	Mang et al.		
		US- 6461905	10/8/2002	Wang et al.		
		<sup>US-</sup> 6617639	9/9/2003	Wang et al.		
	/	<sup>US-</sup> 6642066	11/4/2003	Halliyal et al.		
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INF	ORMATION	DIS	CLOSURE	Filing Date	January 21, 2004	
STA	STATEMENT BY APPLICANT			First Named Inventor	Mohklesi	
				Art Unit	2827	
(Use as many sheets as necessary)			iecessary)	Examiner Name	Huan Hoang	
Sheet	3	of	5	Attorney Docket Number	SAND-01021US0	

			NON PATENT LITERATURE DOCUMENTS					
Examiner Cite No.		Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.					
		<i>*</i>	BORSON, et al., "Direct Measurement of the Energy Distribution of Hot Electrons in Silicon Dioxide," J. Appl. Phys., Vol. 58, No. 3.1, August 1985, pp. 1302-1313	•				
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Substitute to total 1448/FTO				Application Number	10/762,181	
INF	ORMATION	N DIS	CLOSURE	Filing Date	January 21, 2004	
STA	STATEMENT BY APPLICANT			First Named Inventor	Mohklesi .	
				Art Unit	2827	
	(Use as many sheets as necessary)			Examiner Name	thean Hoang	
Sheet	4	of	5	Attorney Docket Number	SAND-01021US0	

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SUBSULU	to to tomi 1448/F10			Application Number	10/762,181	
INF	ORMATION	DIS	CLOSURE	Filing Date	January 21, 2004	
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Sheet	5	of	5	Attorney Docket Number	SAND-01021US0	

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<u>-</u>		NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
44		BUCKLEY, et al., "Engineering of 'Conduction Band-Crested Barriers' or 'Dielectric Constant-Crested Barriers' in view of their application to floating-gate non-volatile memory devices," pp. 55-56.	
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Sheet 1

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